

## INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

# 2SK3530

## • FEATURES

- With TO-220F packaging
- High speed switching
- · Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Power supply
- Switching applications

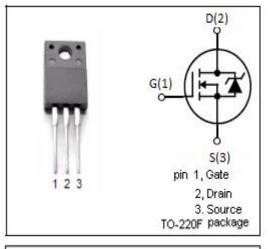
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

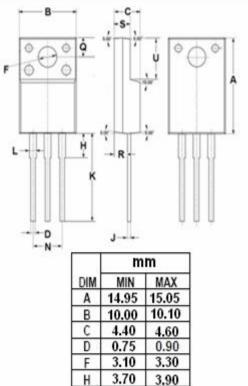
| SYMBOL           | PARAMETER                      | VALUE          | UNIT |  |
|------------------|--------------------------------|----------------|------|--|
| V <sub>DSS</sub> | Drain-Source Voltage           | ce Voltage 800 |      |  |
| V <sub>GSS</sub> | Gate-Source Voltage            | ±30            | v    |  |
| Ισ               | Drain Current-Continuous       | 799            | А    |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed    | 28             | А    |  |
| PD               | Total Dissipation              | 70             | W    |  |
| Tj               | Operating Junction Temperature | 150            | °C   |  |
| T <sub>stg</sub> | Storage Temperature            | -55~150        | °C   |  |

#### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                             | MAX  | UNIT         |  |
|-----------|---------------------------------------|------|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance    | 1.79 | °C <b>/W</b> |  |
| Rth(ch-a) | Channel-to-ambient thermal resistance |      | °C/W         |  |

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0.50

13.4 1.10

5.00

2.70

2.20

2.65

6.40

J

L

Ν

Q

R

<u>s</u>

0.70

13.6

1.30

5.20

2.90

2.40

2.90

6.60

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## ELECTRICAL CHARACTERISTICS

 $T_{C}\text{=}25^{\circ}\!\!\!\mathbb{C}$  unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS  | MIN | ТҮР | МАХ  | UNIT |
|----------------------|--------------------------------|---|-----|-----|------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA              | 800 |     |      | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA | 3.0 |     | 5.0  | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =3.5A               |     |     | 1.9  | Ω    |
| lgss                 | Gate-Source Leakage Current    | V <sub>GS</sub> =±30V;V <sub>DS</sub> =0V                 |     |     | ±0.1 | μA   |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 800V; V <sub>GS</sub> = 0V              |     |     | 50   | μA   |
| VSDF                 | Diode forward voltage          | $I_{SD}=7A$ , $V_{GS}=0$ V                                |     |     | 1.5  | V    |

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